

Part Number	Customer
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Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	100.00 +/- 0.20 mm	
	2.0 Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0 Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0 Secondary Flat Orientation	none/semi standard	
	5.0 Secondary Flat Length	None / 18.0mm +/- 2.0mm	Wafer Vendor
	6.0 Overall Thickness	589.00 +/- 8.00 μ m	ADE, 100%
	7.0 Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	8.0 Bow	<80.00 μ m	ADE to ASTM F534, 20%
	9.0 Warp	<80.00 μ m	ADE to ASTM F657, 20%
	10.0 Edge Chips	0	Bright Light, 100% (note 2)
	11.0 Edge Exclusion	5mm	
HandleSilicon	12.0 Handle Growth Method	CZ	Wafer Vendor
	13.0 Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	14.0 Handle Thickness	500.00 +/- 5.00 μ m	ADE, 100%
	15.0 Handle Doping Type	N	Wafer Vendor
	16.0 Handle Dopant	Arsenic	Wafer Vendor
	17.0 Handle Resistivity	<0.005 Ohmcm	Wafer Vendor
	18.0 Backside Finish	Polished with lasermarking	Guaranteed by Process
DeviceSilicon	20.0 Device Growth Method	FZ	Wafer Vendor
	21.0 Device Orientation	{100} +/- 1 degree	Wafer Vendor
	22.0 Nominal Thickness	70.00 +/- 2.00 μ m	FTIR, 100%. No Offset added.
	23.0 Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	24.0 Device Doping Type	N	Wafer Vendor
	25.0 Device Dopant	Phosphorous	Wafer Vendor
	26.0 Device Resistivity	>5000 Ohmcm	Wafer Vendor
DeviceSilicon2	27.0 Device 2 Growth Method	CZ	Wafer Vendor
	28.0 Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	29.0 Device 2 Nominal Thickness	25.00 +/- 1.00 μ m	ADE Single point, 100%. 6um into Device1.
	30.0 Device 2 DopingType	P	Wafer Vendor
	31.0 Device 2 Dopant	Boron	Wafer Vendor
	32.0 Device 2 Resistivity	<0.005 Ohm cm	Wafer Vendor
DeviceSilicon	33.0 Voids	none	Wafer Vendor
	34.0 Scratches	0	Bright Light, 100% (note 2)
	35.0 Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information